

SPECIFICATION

Device Name : IGBT Module
 Type Name : 7MBR25SA140-01
 Spec. No. : MS6M 0550
 Date : Jun. - 02 - 2000

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Fuji Electric Co., Ltd.
 Matsumoto Factory

DATE		NAME	APPROVED	Fuji Electric Co.,Ltd		
DRAWN	Jun. - 2 - '00	T. Kikugashira	T. Kikugashira	DWG. NO.	MS6M 0550	1 / 10
CHECKED	June - 2 - 00	D. Nishida				a



Revised Records

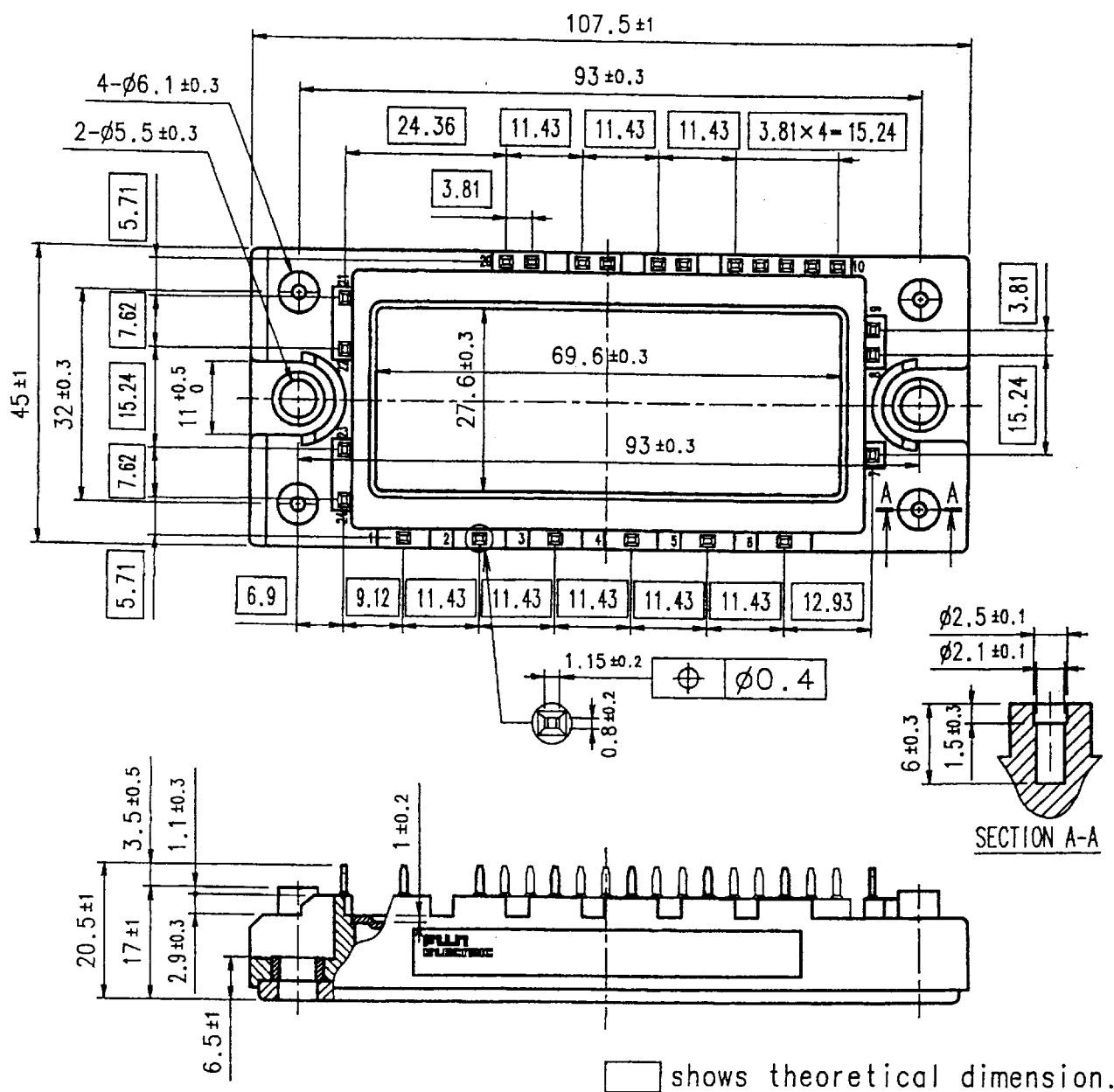
Date	Classi- fication	Ind.	Content	Applied date	Drawn	Checked	Approved
Jun.-2-'00	enactment	—	—	Issued date	—	S. Nitta	T. Miyasaka
Jun.-14-'00	Revision	a	Revised rye miss (P5/10)		J. Kobayashi	S. Nitta	T. Miyasaka

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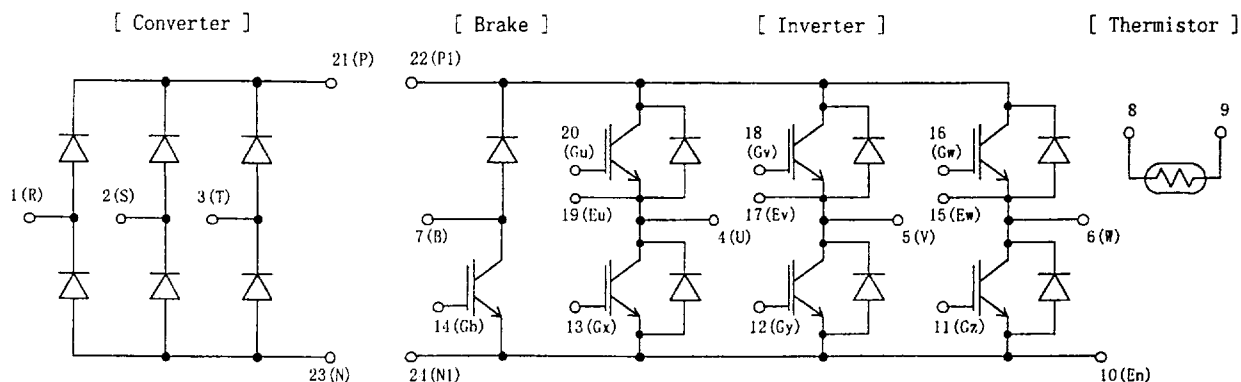
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7MBR25SA140-01

1. Outline Drawing (Unit : mm)



2. Equivalent circuit



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3. Absolute Maximum Ratings (at Tc= 25C unless otherwise specified)

Items		Symbols	Conditions		Maximum Ratings	Units
Inverter	Collector-Emitter voltage	VCES			1400	V
	Gate-Emitter voltage	VGES			+ -20	V
	Collector current	Ic	Continuous	Tc=25C	35	A
				Tc=75C	25	
		Icp	1ms	Tc=25C	70	A
				Tc=75C	50	
	Collector Power Dissipation	-Ic			25	A
Brake	Collector-Emitter voltage	Pc	1 device		180	W
	Gate-Emitter voltage	VCES			1400	V
	Gate-Emitter voltage	VGES			+ -20	V
	Collector current	Ic	Continuous	Tc=25C	25	A
				Tc=75C	15	
		Icp	1ms	Tc=25C	50	A
				Tc=75C	30	
	Collector Power Dissipation	Pc	1 device		110	W
Converter	Repetitive peak reverse Voltage(Diode)	VRRM			1400	V
	Repetitive peak reverse Voltage	VRRM			1600	V
	Average Output Current	Io	50Hz/60Hz sine wave		25	A
	Surge Current (Non-Repetitive)	IFSM	Tj=150C, 10ms		260	A
	I ² t (Non-Repetitive)	I ² t	half sine wave		338	A ² s
Junction temperature		Tj			150	C
Storage temperature		Tstg			-40~ +125	C
Isolation voltage	between terminal and copper base ^{(*)1}	Viso	AC : 1min.		2500	V
	between thermistor and others ^{(*)2}				2500	V
Mounting Screw Torque ^{(*)3}					3.5	Nm

(*)1 All terminals should be connected together when isolation test will be done.

(*)2 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

(*)3 Recommendable Value : 2.5~3.5 Nm (M5)

4. Electrical characteristics (at Tj= 25C unless otherwise specified)

	Items	Symbols	Conditions	Characteristics			Units
				min.	typ.	Max.	
Inverter	Zero gate voltage Collector current	ICES	VGE = 0 V, VCE ^(a) 1400 V			1.0	mA
	Gate-Emitter leakage current	IGES	VCE = 0 V, VGE +20 V			200	nA
	Gate-Emitter threshold voltage	VGE(th)	VCE = 20 V, Ic = 25 mA	5.5	7.2	8.5	V
	Collector-Emitter saturation voltage	VCE(sat)	VGE = 15 V, chip		2.2		V
			Ic = 25 A terminal		2.3	2.7	
	Input capacitance	Cies	VGE = 0 V, VCE = 10 V f = 1 MHz		3000		pF
	Turn-on time	ton	Vcc = 800 V		0.35	1.2	us
		tr	Ic = 25 A		0.25	0.6	
		tr(0)	VGE +-15 V		0.1		
	Turn-off time	toff	RG = 51 ohm		0.45	1.0	
		tf			0.08	0.3	
Brake	Forward on voltage	VF	IF = 25 A chip		2.4		V
			terminal		2.5	3.3	
	Reverse recovery time	trr	IF = 25 A			350	ns
	Zero gate voltage Collector current	ICES	VGE = 0 V, VCE ^(a) 1400 V			1.0	mA
	Gate-Emitter leakage current	IGES	VCE = 0 V, VGE +20 V			200	nA
	Collector-Emitter saturation voltage	VCE(sat)	VGE = 15 V, chip		2.2		V
			Ic = 15 A terminal		2.3	2.7	
	Turn-on time	ton	Vcc = 800 V		0.35	1.2	us
		tr	Ic = 15 A		0.25	0.6	
	Turn-off time	toff	VGE +-15 V		0.45	1.0	
		tf	RG = 82 ohm		0.08	0.3	
Converter	Reverse current	IRRM	VR = 1400 V			1.0	mA
	Forward on voltage	VFM	IF = 25 A chip		1.1		V
			terminal		1.2	1.5	
Thermistor	Reverse current	IRRM	VR = 1600 V			1.0	mA
	Resistance	R	T = 25C		5000		ohm
			T = 100C	465	495	520	
	B value	B	T = 25/50C	3305	3375	3450	K

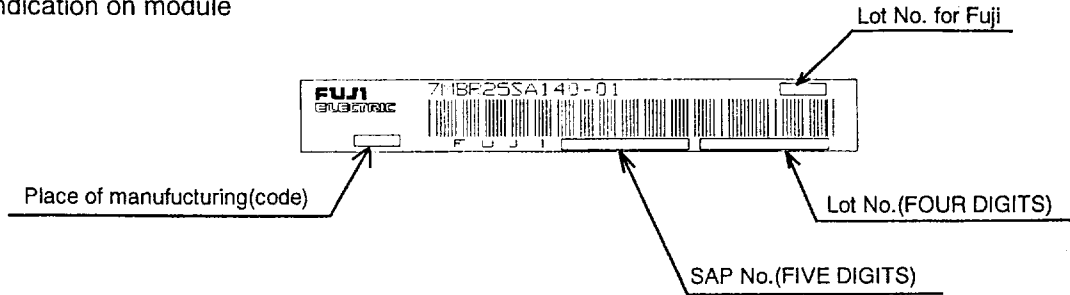
5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	Max.	
Thermal resistance (1 device)	Rth(j-c)	Inverter IGBT			0.69	C/W
		Inverter FWD			1.30	
		Brake IGBT			1.14	
		Converter Diode			0.90	
Contact Thermal resistance	Rth(c-f)	with Thermal Compound ^(*)		0.05		C/W

* This is the value which is defined mounting on the additional cooling fin with thermal compound.

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6. Indication on module



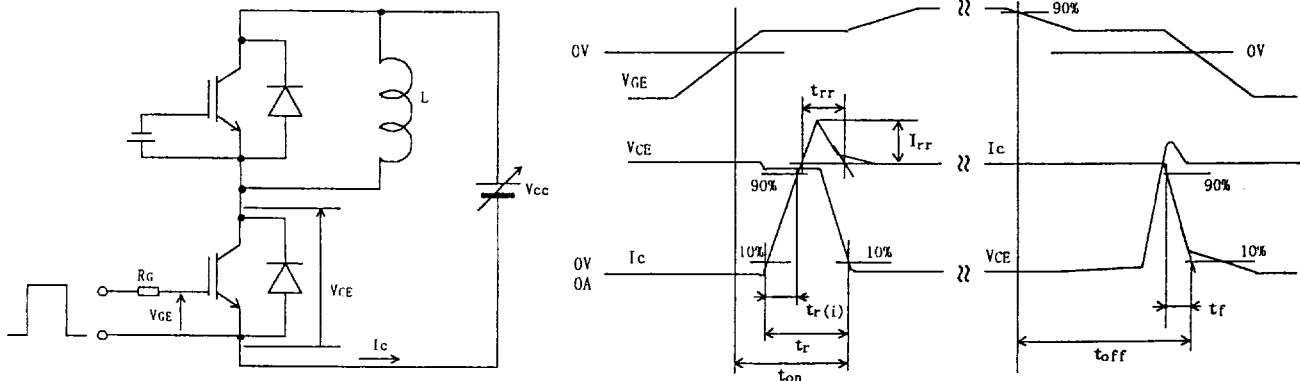
7. Applicable category

This specification is applied to Power Integrated Module named 7MBR25SA140-01 .

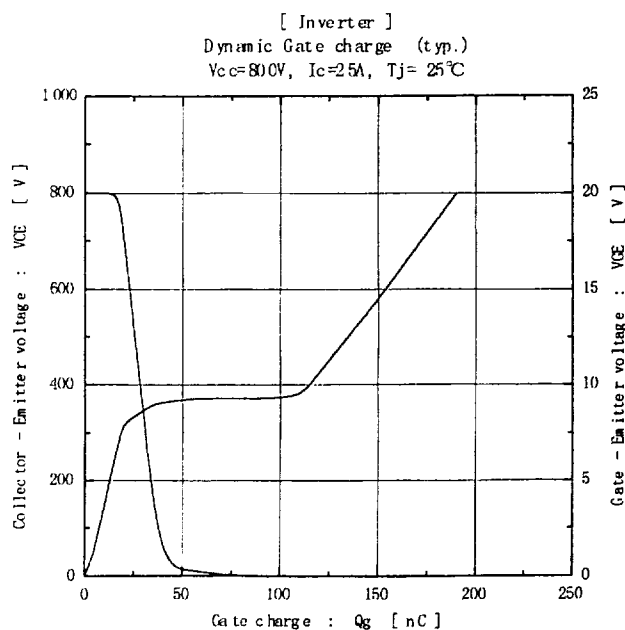
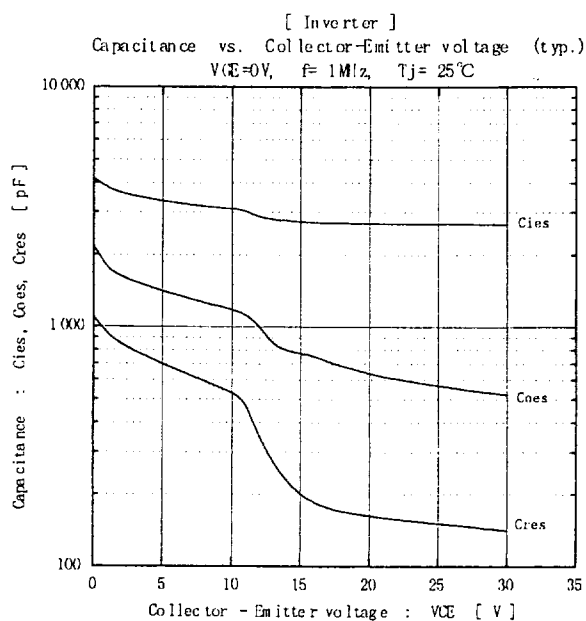
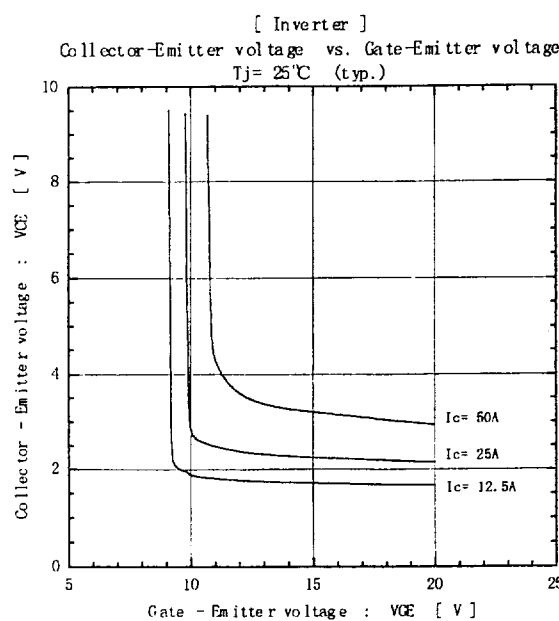
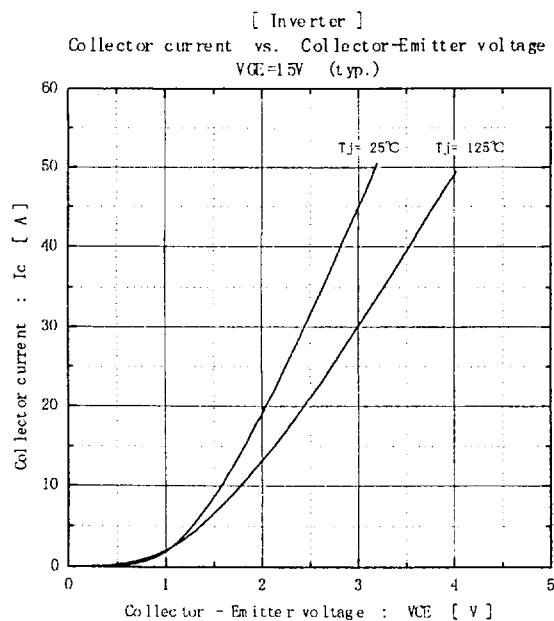
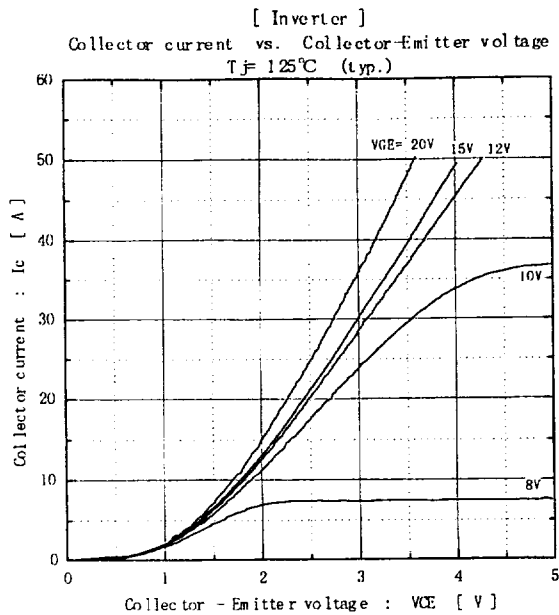
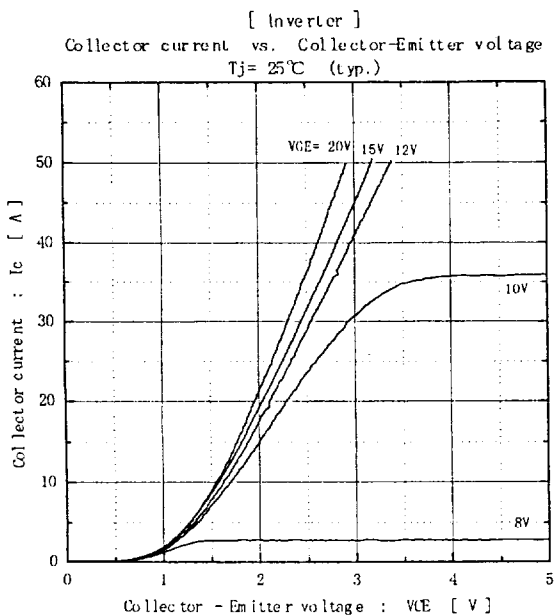
8. Storage and transportation notes

- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
- Avoid exposure to corrosive gases and dust.
- Avoid excessive external force on the module.
- Store modules with unprocessed terminals.
- Do not drop or otherwise shock the modules when transporting.
- Please connect adequate fuse or protector of circuit between three-phase line and this product to prevent the equipment from causing secondary destruction.

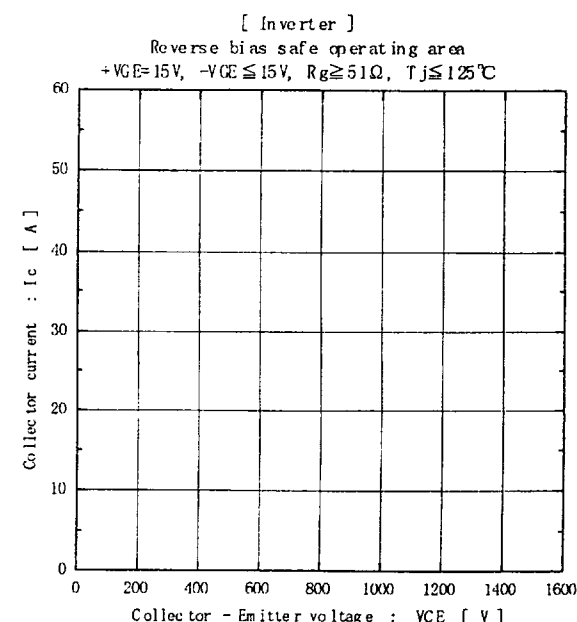
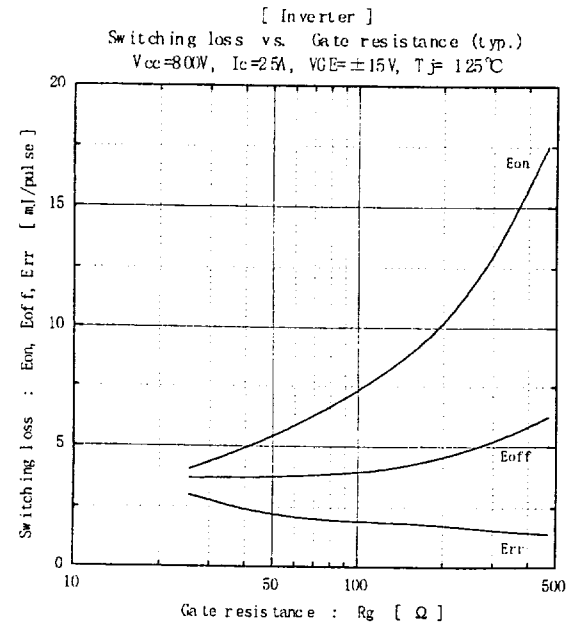
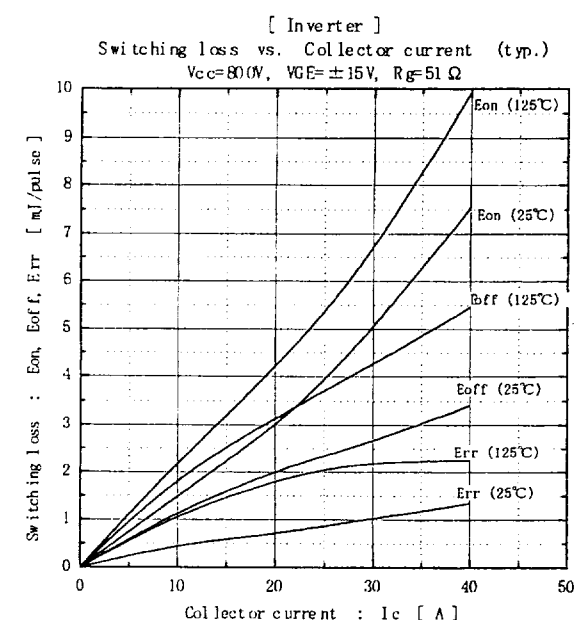
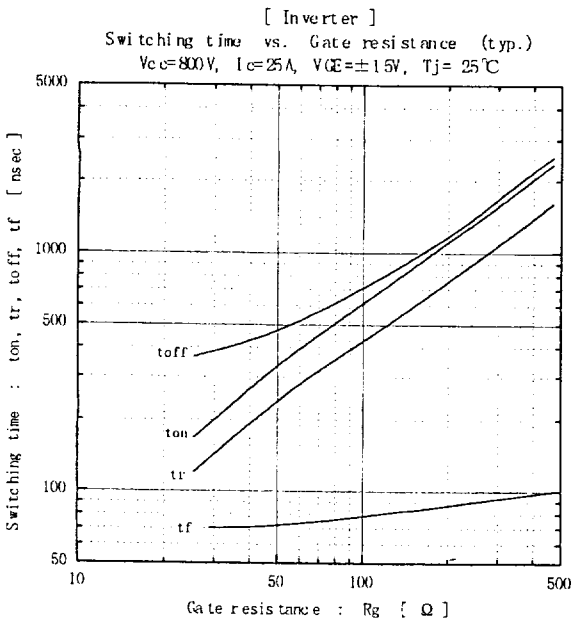
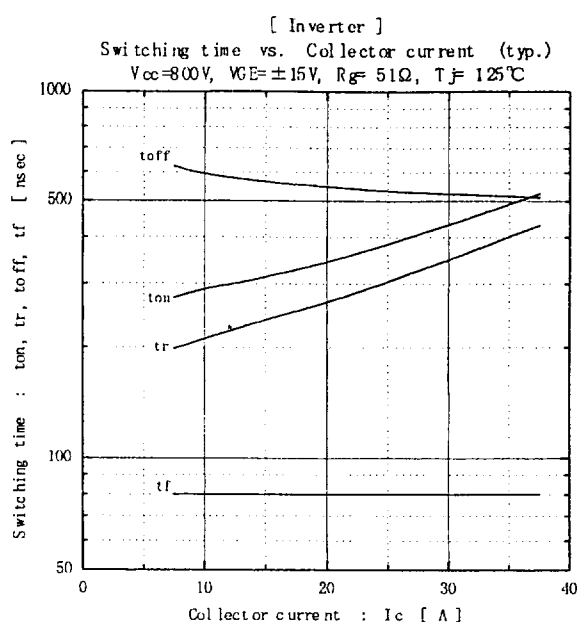
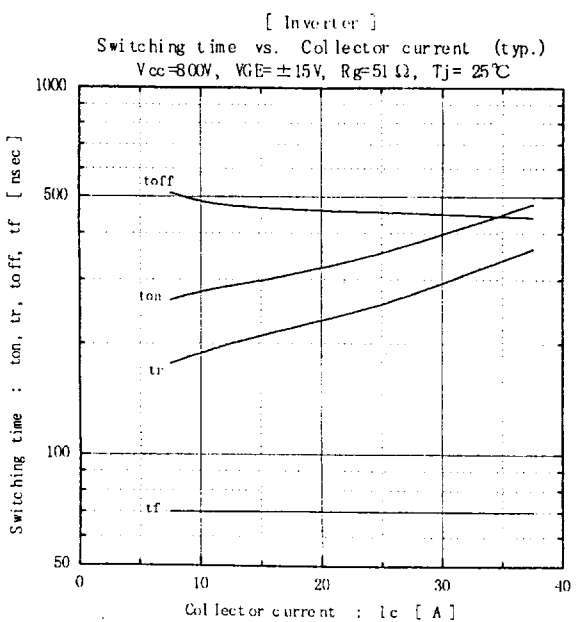
9. Definitions of switching time



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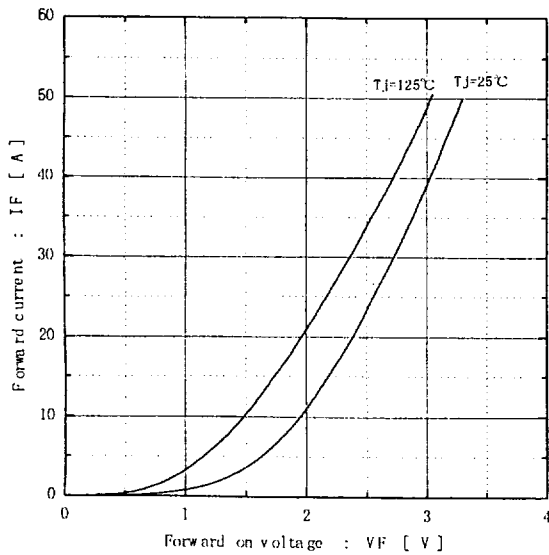


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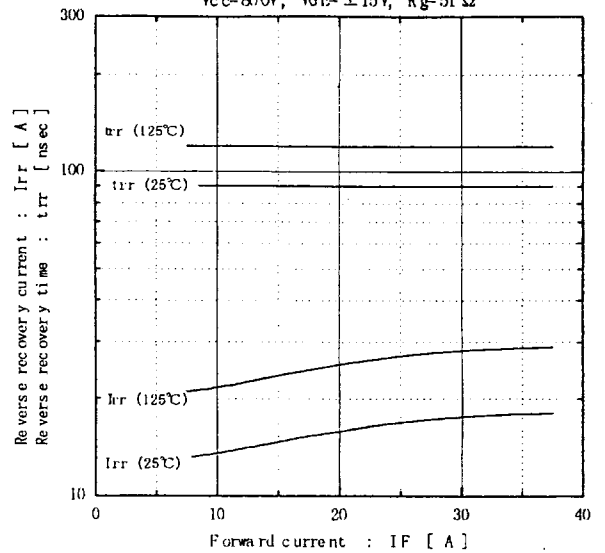


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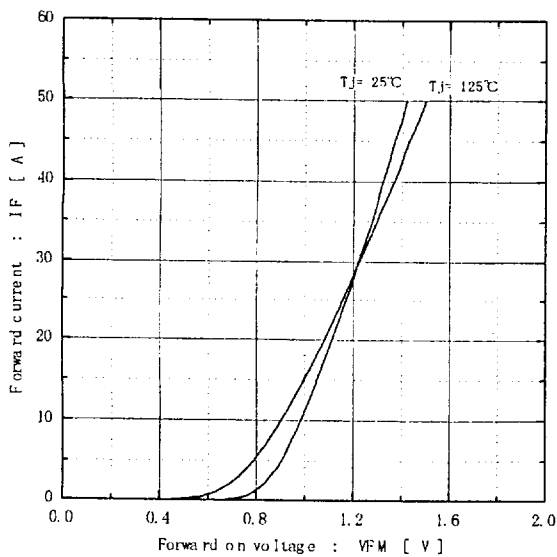
[Inverter]
Forward current vs. Forward on voltage (typ.)



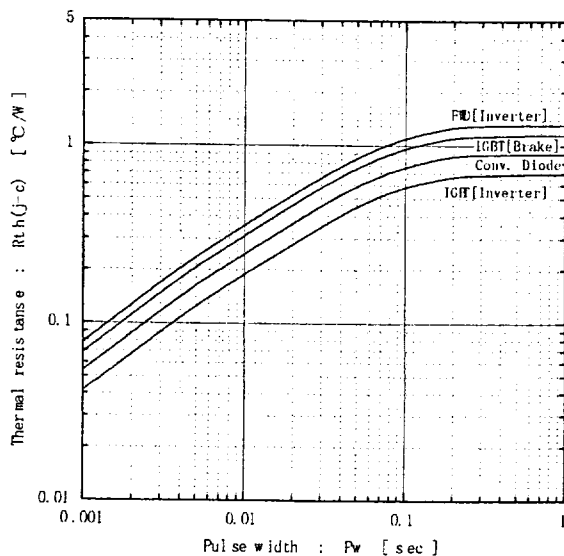
[Inverter]
Reverse recovery characteristics (typ.)
 $V_C = 800V$, $V_{GE} = \pm 15V$, $R_g = 51\Omega$



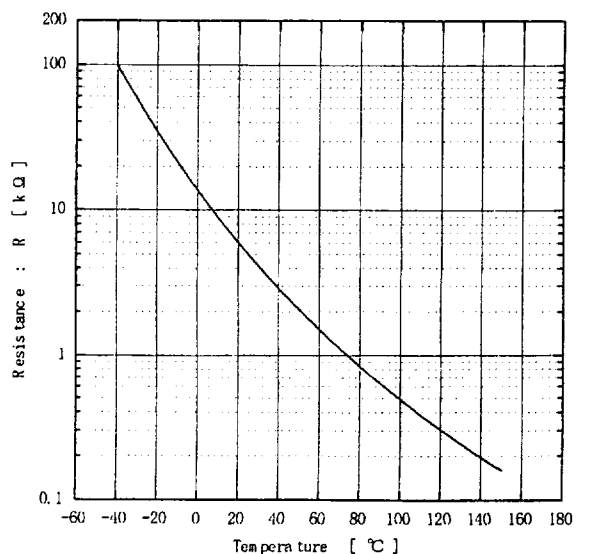
[Converter]
Forward current vs. Forward on voltage (typ.)



Transient thermal resistance



[Thermistor]
Temperature characteristic (typ.)



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